

Xiabing Lou

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	High-Performance InAlN/GaN MOSHEMTs Enabled by Atomic Layer Epitaxy MgCaO as Gate Dielectric. IEEE Electron Device Letters, 2016, 37, 556-559.	3.9	46
2	Atomic layer deposition of Sc ₂ O ₃ for passivating AlGaIn/GaN high electron mobility transistor devices. Applied Physics Letters, 2012, 101, 232109.	3.3	39
3	Epitaxial Growth of Mg _x Ca _{1-x} O on GaN by Atomic Layer Deposition. Nano Letters, 2016, 16, 7650-7654.	9.1	30
4	Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. Angewandte Chemie - International Edition, 2016, 55, 10228-10233.	13.8	29
5	DC and RF Performance of AlGaIn/GaN/SiC MOSHEMTs With Deep Sub-Micron T-Gates and Atomic Layer Epitaxy MgCaO as Gate Dielectric. IEEE Electron Device Letters, 2017, 38, 1409-1412.	3.9	27
6	Enhancement-Mode AlGaIn/GaN Fin-MOSHEMTs on Si Substrate With Atomic Layer Epitaxy MgCaO. IEEE Electron Device Letters, 2017, 38, 1294-1297.	3.9	20
7	Direct-Liquid-Evaporation Chemical Vapor Deposition of Nanocrystalline Cobalt Metal for Nanoscale Copper Interconnect Encapsulation. ACS Applied Materials & Interfaces, 2017, 9, 10914-10920.	8.0	17
8	Study of the crystal structure of SnS thin films by atomic layer deposition. AIP Advances, 2021, 11, .	1.3	14
9	Total-Ionizing-Dose Responses of GaN-Based HEMTs With Different Channel Thicknesses and MOSHEMTs With Epitaxial MgCaO as Gate Dielectric. IEEE Transactions on Nuclear Science, 2018, 65, 46-52.	2.0	12
10	Band-Offset Analysis of Atomic Layer Deposition La ₂ O ₃ on GaAs(111), (110), and (100) Surfaces for Epitaxial Growth. ACS Applied Materials & Interfaces, 2019, 11, 28515-28519.	8.0	9
11	Atomic layer deposition of cubic tin-calcium sulfide alloy films. Journal of Materials Research, 2020, 35, 795-803.	2.6	6
12	Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. Angewandte Chemie, 2016, 128, 10384-10389.	2.0	4
13	Total Ionizing Dose (TID) Effects in GaAs MOSFETs With La-Based Epitaxial Gate Dielectrics. IEEE Transactions on Nuclear Science, 2017, 64, 164-169.	2.0	4
14	InAlN/GaN MOSHEMTs with high drain current of 2.3 A/mm high on/off ratio of 10 ¹² and low SS of 64 mV/dec enabled by atomic-layer-epitaxial MgCaO as gate dielectric. , 2015, .		1
15	ALD Growth of Mg _x Ca _{1-x} O on GaN and Its Band Offset Analysis. ACS Applied Electronic Materials, 2021, 3, 845-853.	4.3	1
16	Frontispiece: Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. Angewandte Chemie - International Edition, 2016, 55, .	13.8	0
17	Frontispiz: Synthesis of Calcium(II) Amidinate Precursors for Atomic Layer Deposition through a Redox Reaction between Calcium and Amidines. Angewandte Chemie, 2016, 128, .	2.0	0
18	Epitaxial growth of Mg _x Ca _{1-x} O on 4H-SiC(0001) and In ₂ Ga ₂ O ₃ wide band gap semiconductors with atomic layer deposition. Journal of Materials Research, 2020, 35, 831-839.	2.6	0